

PATENT

Attorney Docket No.: A7632/T49100
AMAT No.: 007632 USA/DSM/HDP/CVD/JW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

FARHAD K. MOGHADAM et al.

Application No.: Unassigned

Filed: Herewith

For: SEQUENTIAL GAS FLOW OXIDE
DEPOSITION TECHNIQUE

Examiner: Unassigned

Art Unit: Unassigned

**INFORMATION DISCLOSURE
STATEMENT UNDER 37 CFR §1.97 and
§1.98**

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

The references cited on attached form PTO/SB/08A and PTO/SB/08B are being called to the attention of the Examiner. Copies of the references are enclosed. It is respectfully requested that the cited references be expressly considered during the prosecution of this application, and the references be made of record therein and appear among the "references cited" on any patent to issue therefrom.

As provided for by 37 CFR 1.97(g) and (h), no representation is being made that a search has been conducted or that this statement encompasses all the possible relevant information, and no inference should be made that the information and references cited are, or are considered to be material to patentability because they are in this statement. No inference should be made that the information and references cited are prior art merely because they are in this statement.

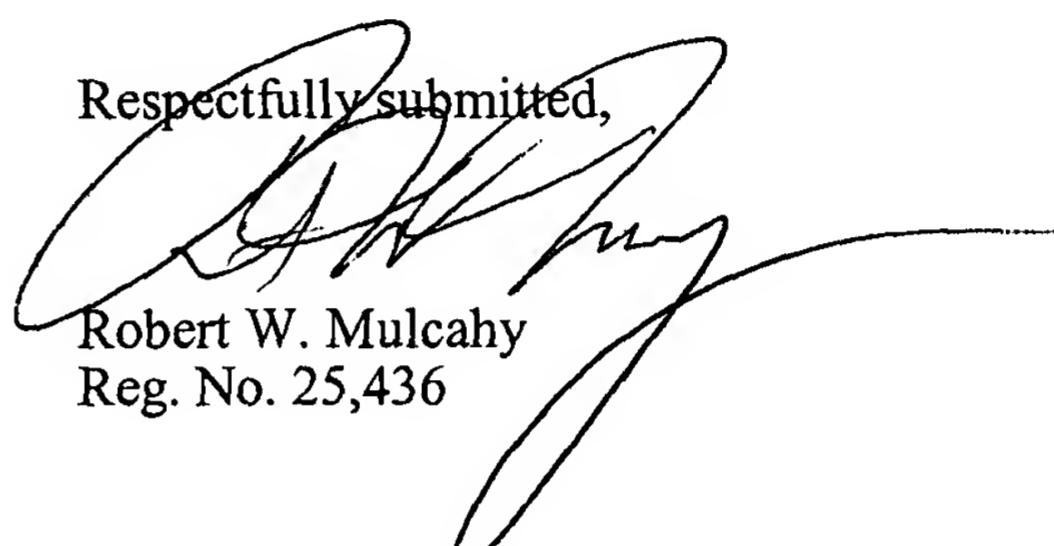
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However, if a fee is required, the Commissioner is authorized to deduct such fee from the undersigned's Deposit Account No. 20-1430. Please deduct any additional fees from, or credit any overpayment to, the above-noted Deposit Account.

Respectfully submitted,


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Substitute for form 1449/PTO		<i>Complete if Known</i>	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>		Application Number	Unassigned
		Filing Date	Filed Herewith
		First Named Inventor	Moghadam, Farhad K., et. al.
		Art Unit	Unassigned
		Examiner Name	Unassigned
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		Attorney Docket Number	A7632/T49100

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code ³	Number ⁴ Kind Code ⁵ (if known)			
	AM	WO	01/40541 A1	06-07-2001		<input type="checkbox"/>
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	AO	WO	01/66832 A2	09-13-2001		<input type="checkbox"/>
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	AQ	EP	526 779 B1	02-10-1993		<input type="checkbox"/>
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Art Unit	Unassigned
Examiner Name	Unassigned

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NON PATENT LITERATURE DOCUMENTS		
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
	AS	"Atomic Layer Deposition" by Physical Inorganic Chemistry, Institute of Applied Synthetic Chemistry, downloaded from website http://www.ias.tuwien.ac.at/research/fghh/research/pic_research_ald.html on 7/23/02
	AT	GEORGE et al., "Atomic layer controlled deposition of SiO ₂ and Al ₂ O ₃ using ABAB... binary reaction sequence chemistry," <i>Applied Surface Science</i> , 82/83:460-467 (1994).
	AU	GEORGE et al., "Surface Chemistry for Atomic Layer Growth," <i>J. Phys. Chem.</i> , 100(31):13121-13131 (1996).
	AV	KLAUS et al., "Atomic Layer Deposition of SiO ₂ Using Catalyzed and Uncatalyzed Self-Limiting Surface Reactions," <i>Surface Review and Letters</i> , 6(3/4):435-448 (1999).
	AW	KLAUS et al., "Atomic layer controlled growth of SiO ₂ films using binary reaction sequence chemistry," <i>Appl. Phys. Lett.</i> , 70(9):1092-1094 (1997).
	AX	MORISHITA et al., "New substances for atomic-layer deposition of silicon dioxide," <i>J. Non-Crystalline Solids</i> , 187:66-69 (1995).
	AY	WISE et al., "Diethyldiethoxysilane as a New Precursor for SiO ₂ Growth on Silicon," from <i>Gas-Phase and SurfaceChemistry in electronic Materials Processing</i> , Mountzaris et al., eds., from Symposium held 11/29/93 thru 12/2/93 in Boston Massachusetts, pages 37-43.
	AZ	YAMAGUCHI et al., "Atomic-layer chemical-vapor-deposition of silicon dioxide films with an extremely low hydrogen content," <i>Applied Surface Science</i> , 130-132:202-207 (1998).

Examiner Signature	Date Considered
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